杭芯科技
HUTCHIP

HC3134KE

20V N-Channel MOSFET

General Description

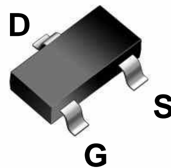
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

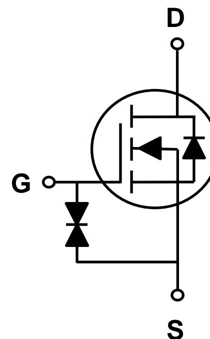
Features

V_{DS}	20V
I_D (at V_{GS}=4.5V)	0.5A
$R_{DS(ON)}$ (at V_{GS}=4.5V)	220mΩ(Typ)

ESD Protected Up to 2.0KV (HBM)

SOT523





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±12	V
Drain Current-Continuous	TC=25°C	I_D	0.5	A
	TC=70°C	I_D	0.4	A
Drain Current – Pulsed		I_{DM}	3.3	A
Maximum Power Dissipation		P_D	0.18	W
Junction and Storage Temperature Range		T_J,T_{STG}	-55 To 150	℃

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance junction-to-solder poin	$R_{\theta Jc}$		40	℃ /W
Thermal Resistance junction-to-Ambient	$R_{\theta JA}$		690	℃ /W

Electrical Characteristics (TJ=25℃ unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V,V_{GS}=0V			1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±10V,V_{DS}=0V			±10	μA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	0.3	0.7	1.2	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=4.5V, I_D=0.5A		220	300	mΩ
		V_{GS}=2.5V, I_D=0.4A		290	400	mΩ
		V_{GS}=1.8V, I_D=0.2A		420	700	mΩ
I_S	Maximum Body-Diode Continuous Current				0.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{DS}=10V,V_{GS}=0V, F=1.0MHz		56		pF
C_{oss}	Output Capacitance			20		pF
C_{rss}	Reverse Transfer Capacitance			2.5		pF
SWITCHING PARAMETERS						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=4.5V V_{DS}=10V R_G=25Ω I_D=0.5A		2		nS
t_r	Turn-on Rise Time			18.8		nS
$t_{d(off)}$	Turn-Off Delay Time			10		nS
t_f	Turn-Off Fall Time			23		nS
Q_g	Total Gate Charge	V_{DS}=10V,I_D=0.5A, V_{GS}=4.5V		1		nC
Q_{gs}	Gate-Source Charge			0.28		nC
Q_{gd}	Gate-Drain Charge			0.2		nC
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_{SD}=1A		0.70	1.3	V

Note：

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

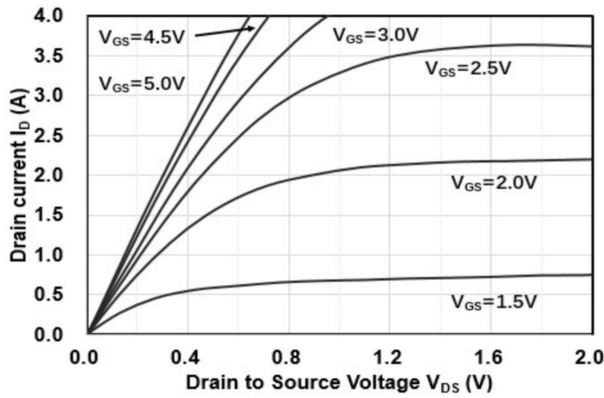


Figure1. Output Characteristics

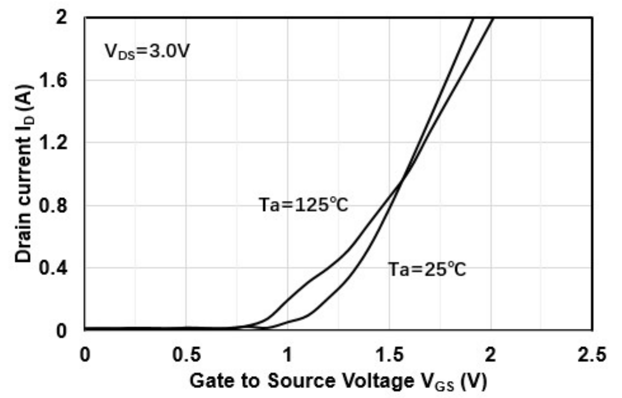


Figure2. Transfer Characteristics

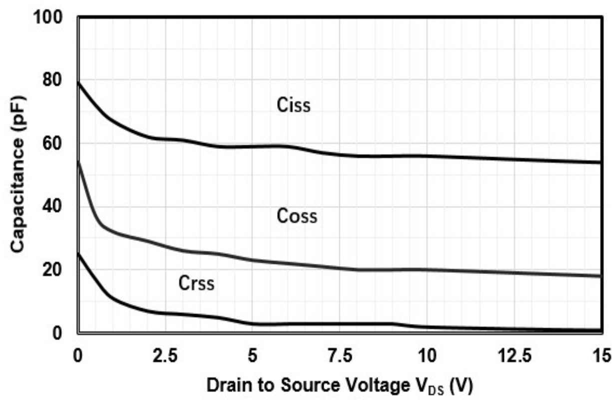


Figure3. Capacitance Characteristics

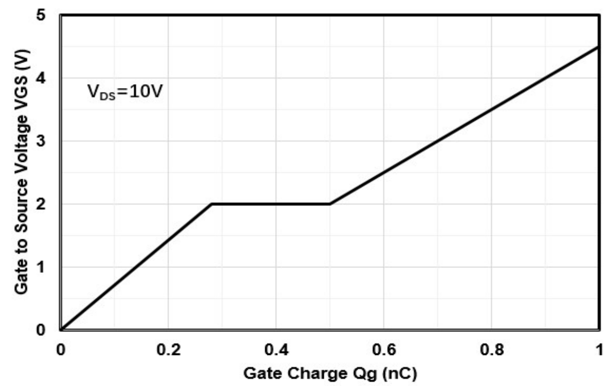


Figure4. Gate Charge

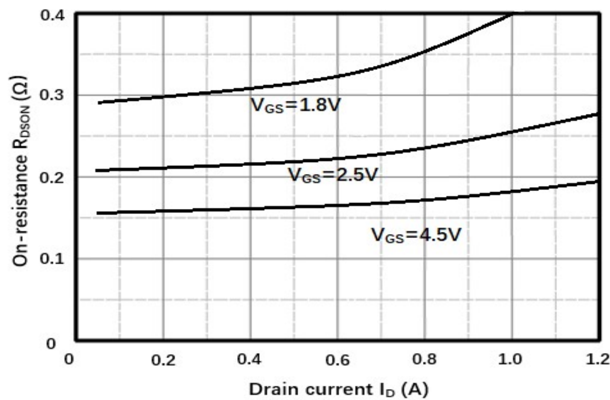


Figure5. Drain-Source on Resistance

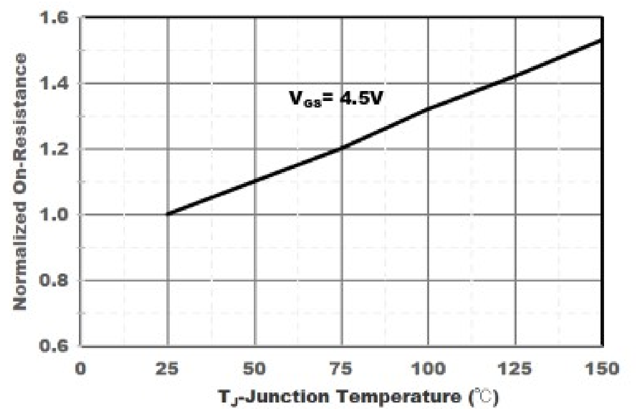


Figure6. Drain-Source on Resistance

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

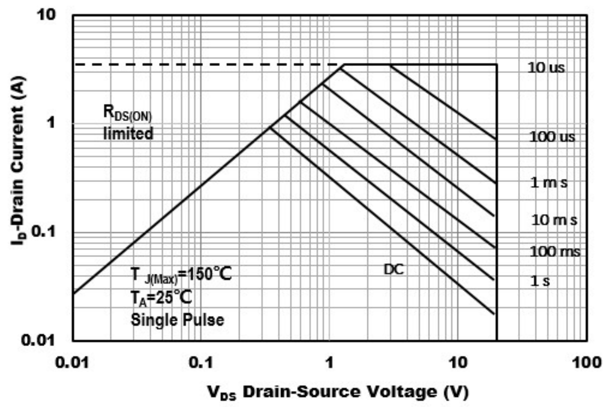


Figure7. Safe Operation Area

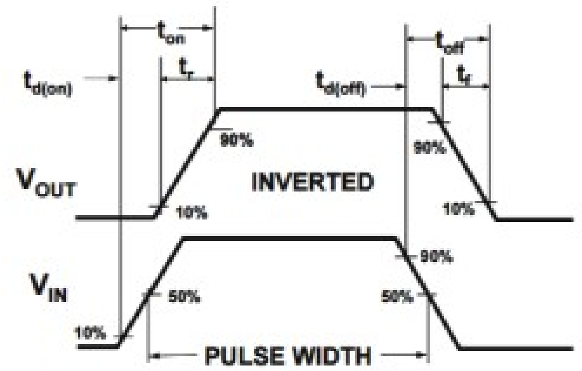
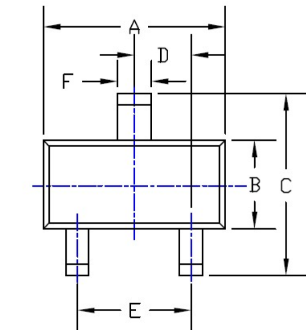
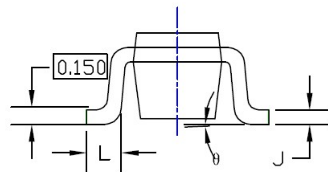


Figure8. Switching wave

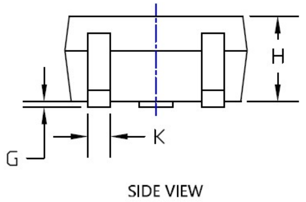
SOT523 PACKAGE INFORMATION



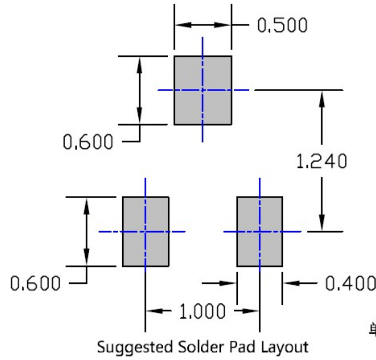
TOP VIEW



SIDE VIEW



SIDE VIEW



Suggested Solder Pad Layout

单位：mm

SYMBOL	DIMENSIONS					
	INCHES			Millmeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.059	0.063	0.067	1.500	1.600	1.700
B	0.030	0.031	0.033	0.750	0.800	0.850
C	0.057	0.063	0.069	1.450	1.600	1.750
D	0.020TYP			0.500TYP		
E	0.035	0.039	0.043	0.900	1.000	1.100
F	0.010	0.014	0.018	0.250	0.350	0.450
G	0.000	---	0.004	0.000	---	0.100
H	0.024	0.028	0.031	0.600	0.700	0.800
J	0.004	---	0.008	0.100	---	0.200
K	0.006	0.010	0.014	0.150	0.250	0.350
L	0.010	---	0.018	0.260	---	0.460
θ	0°	---	8°	0°	---	8°

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.